

Anne Henry

List of Publications by Year in descending order

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papers

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142
docs citations

142
times ranked

815
citing authors

#	ARTICLE	IF	CITATIONS
1	Chloride-Based CVD Growth of Silicon Carbide for Electronic Applications. <i>Chemical Reviews</i> , 2012, 112, 2434-2453.	23.0	99
2	Growth of High Quality Epitaxial Rhombohedral Boron Nitride. <i>Crystal Growth and Design</i> , 2012, 12, 3215-3220.	1.4	60
3	Epitaxial CVD growth of sp^2 -hybridized boron nitride using aluminum nitride as buffer layer. <i>Physica Status Solidi - Rapid Research Letters</i> , 2011, 5, 397-399.	1.2	44
4	Phonon replicas at the Γ point in $4H\text{-}\alpha\text{-SiC}$: A theoretical and experimental study. <i>Physical Review B</i> , 1998, 58, 13634-13647.	1.1	39
5	Fast SiC Epitaxial Growth in a Chimney CVD Reactor and HTCVD Crystal Growth Developments. <i>Materials Science Forum</i> , 2000, 338-342, 131-136.	0.3	33
6	Growth characteristics of chloride-based SiC epitaxial growth. <i>Physica Status Solidi - Rapid Research Letters</i> , 2008, 2, 278-280.	1.2	32
7	Review Article: Challenge in determining the crystal structure of epitaxial 0001 oriented sp^2 -BN films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018, 36, .	0.9	32
8	Electron paramagnetic resonance and theoretical studies of shallow phosphorous centers in $3C$ -, $4H$ -, and $6H\text{-}\alpha\text{-SiC}$. <i>Physical Review B</i> , 2006, 73, .	1.1	31
9	Micropipe Healing in Liquid Phase Epitaxial Growth of SiC. <i>Materials Science Forum</i> , 2000, 338-342, 237-240.	0.3	28
10	Material characterization need for SiC-based devices. <i>Materials Science in Semiconductor Processing</i> , 2001, 4, 181-186.	1.9	28
11	A SiC Varactor With Large Effective Tuning Range for Microwave Power Applications. <i>IEEE Electron Device Letters</i> , 2011, 32, 788-790.	2.2	26
12	Polytype Pure sp^2 -BN Thin Films As Dictated by the Substrate Crystal Structure. <i>Chemistry of Materials</i> , 2015, 27, 1640-1645.	3.2	26
13	Very high crystalline quality of thick $4H\text{-}\alpha\text{-SiC}$ epilayers grown from methyltrichlorosilane (MTS). <i>Physica Status Solidi - Rapid Research Letters</i> , 2008, 2, 188-190.	1.2	24
14	Chloride-based CVD of $3C\text{-}\alpha\text{-SiC}$ epitaxial layers on $6H(0001)$ SiC. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010, 4, 305-307.	1.2	24
15	Influence of Epitaxial Growth and Substrate Induced Defects on the Breakdown of High-voltage $4H\text{-SiC}$ Schottky Diodes. <i>Materials Science Forum</i> , 2000, 338-342, 1175-1178.	0.3	23
16	On the effect of silicon in CVD of sp^2 -hybridized boron nitride thin films. <i>CrystEngComm</i> , 2013, 15, 455-458.	1.3	23
17	High Growth Rate of $4H\text{-SiC}$ Epilayers on On-Axis Substrates with Different Chlorinated Precursors. <i>Crystal Growth and Design</i> , 2010, 10, 5334-5340.	1.4	22
18	Low Temperature CVD of Thin, Amorphous Boron-Carbon Films for Neutron Detectors. <i>Chemical Vapor Deposition</i> , 2012, 18, 221-224.	1.4	22

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19	Investigations of Possible Nitrogen Participation in the Z₁/Z₂ Defect in 4H-SiC. Materials Science Forum, 2004, 457-460, 469-472.	0.3	21
20	Double-Position-Boundaries Free 3C-SiC Epitaxial Layers Grown on On-Axis 4H-SiC. ECS Journal of Solid State Science and Technology, 2014, 3, P75-P81.	0.9	21
21	Photoluminescence of the two-dimensional hole gas in p-type $\hat{\Gamma}$ -doped Si layers. Physical Review B, 1996, 53, 9587-9590.	1.1	18
22	Growth and Characterisation of SiC Power Device Material. Materials Science Forum, 1998, 264-268, 97-102.	0.3	18
23	Characterization of Bulk and Epitaxial SiC Material Using Photoluminescence Spectroscopy. Materials Science Forum, 2002, 389-393, 593-596.	0.3	18
24	High Voltage (>2.5kV) 4H-SiC Schottky Rectifiers Processed on Hot-Wall CVD and High-Temperature CVD Layers. Materials Science Forum, 1998, 264-268, 921-924.	0.3	17
25	CVD Growth and Characterisation of SiC Epitaxial Layers on Faces Perpendicular to the (0001) Basal Plane. Materials Science Forum, 1998, 264-268, 123-126.	0.3	17
26	Homoepitaxial Growth of 4H-SiC on On-Axis Si-Face Substrates Using Chloride-Based CVD. Materials Science Forum, 0, 600-603, 107-110.	0.3	17
27	Comparative Studies of Carrier Dynamics in 3C-SiC Layers Grown on Si and 4H-SiC Substrates. Journal of Electronic Materials, 2011, 40, 394-399.	1.0	17
28	Gas-Phase Modeling of Chlorine-Based Chemical Vapor Deposition of Silicon Carbide. Crystal Growth and Design, 2012, 12, 1977-1984.	1.4	17
29	Initial stages of growth and the influence of temperature during chemical vapor deposition of sp ² -BN films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	17
30	SiC Varactors for Dynamic Load Modulation of High Power Amplifiers. IEEE Electron Device Letters, 2008, 29, 728-730.	2.2	15
31	Electrical Characterization of the Gallium Acceptor in 4H- and 6H-SiC. Materials Science Forum, 1998, 264-268, 557-560.	0.3	14
32	Optical identification and electronic configuration of tungsten in 4H- and 6H-SiC. Physica B: Condensed Matter, 2012, 407, 1462-1466.	1.3	14
33	Chloride-Based SiC Epitaxial Growth toward Low Temperature Bulk Growth. Crystal Growth and Design, 2010, 10, 3743-3751.	1.4	13
34	SiC epitaxy growth using chloride-based CVD. Physica B: Condensed Matter, 2012, 407, 1467-1471.	1.3	13
35	Growth and Characterisation of Thick SiC Epilayers by High Temperature CVD. Materials Science Forum, 1998, 264-268, 103-106.	0.3	12
36	Epitaxial Growth and Characterisation of Phosphorus Doped SiC Using TBP as Precursor. Materials Science Forum, 2005, 483-485, 101-104.	0.3	12

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37	Carrier Removal in Electron Irradiated 4H and 6H SiC. Materials Science Forum, 2008, 600-603, 425-428.	0.3	12
38	On the effect of water and oxygen in chemical vapor deposition of boron nitride. Thin Solid Films, 2012, 520, 5889-5893.	0.8	12
39	Thickness Contour Mapping of SiC Epi-Films on SiC Substrates. Materials Science Forum, 1998, 264-268, 645-648.	0.3	11
40	Electrothermal actuation of silicon carbide ring resonators. Journal of Vacuum Science & Technology B, 2009, 27, 3109.	1.3	11
41	Excitation properties of hydrogen-related photoluminescence in 6H-SiC. Physical Review B, 2000, 62, 7162-7168.	1.1	10
42	Growth and Properties of SiC On-Axis Homoepitaxial Layers. Materials Science Forum, 2010, 645-648, 83-88.	0.3	10
43	Metastability of a Hydrogen-related Defect in 6H-SiC. Materials Science Forum, 2000, 338-342, 651-654.	0.3	9
44	Investigation of an Ion-Implantation Induced High Temperature Persistent Intrinsic Defect in SiC. Materials Science Forum, 2001, 353-356, 377-380.	0.3	9
45	Fabrication of beam resonators from hot-wall chemical vapour deposited SiC. Microelectronic Engineering, 2009, 86, 1194-1196.	1.1	9
46	Surface Preparation of 4° Off-Axis 4H-SiC Substrate for Epitaxial Growth. Materials Science Forum, 0, 740-742, 225-228.	0.3	9
47	Effect of ion bombardment on deep photoluminescence bands in p-type boron-modulation-doped Si layers grown by molecular-beam epitaxy. Physical Review B, 1995, 52, 12006-12012.	1.1	8
48	High Growth Rate Epitaxy of Thick 4H-SiC Layers. Materials Science Forum, 2000, 338-342, 165-168.	0.3	8
49	Presence of Hydrogen in SiC. Materials Science Forum, 2001, 353-356, 373-376.	0.3	8
50	SiC and III-Nitride Growth in Hot-Wall CVD Reactor. Materials Science Forum, 2005, 483-485, 61-66.	0.3	8
51	Electrical Characterization of PiN Diodes with p ⁺ Layer Selectively Grown by VLS Transport. Materials Science Forum, 2013, 740-742, 911-914.	0.3	8
52	Early stages of growth and crystal structure evolution of boron nitride thin films. Japanese Journal of Applied Physics, 2016, 55, 05FD06.	0.8	8
53	S-Cu-related metastable complex defect in Si by optical detection of magnetic resonance. Physical Review B, 1994, 50, 7365-7370.	1.1	7
54	Designing, Physical Simulation and Fabrication of High-Voltage (3.85 kV) 4H-SiC Schottky Rectifiers Processed on Hot-Wall and Chimney CVD Films. Materials Science Forum, 2000, 338-342, 1171-1174.	0.3	7

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55	4H-SiC Epitaxial Layers Grown on On-Axis Si-Face Substrate. Materials Science Forum, 2007, 556-557, 53-56.	0.3	7
56	Growth of Thick 4H-SiC Epitaxial Layers on On-Axis Si-Face Substrates with HCl Addition. Materials Science Forum, 2009, 615-617, 93-96.	0.3	7
57	Bistable defects in low-energy electron irradiated n-type 4H-SiC. Physica Status Solidi - Rapid Research Letters, 2010, 4, 227-229.	1.2	7
58	Chloride-Based CVD at High Growth Rates on Vicinal Off-Angles SiC Wafers. Materials Science Forum, 0, 645-648, 107-110.	0.3	7
59	Chloride-Based CVD at High Rates of 4H-SiC on On-Axis Si-Face Substrates. Materials Science Forum, 2011, 679-680, 59-62.	0.3	7
60	Carrot Defect Control in Chloride-Based CVD through Optimized Ramp up Conditions. Materials Science Forum, 0, 717-720, 109-112.	0.3	7
61	3C-SiC Heteroepitaxy on Hexagonal SiC Substrates. Materials Science Forum, 2013, 740-742, 257-262.	0.3	7
62	Cathodoluminescence of Defect Regions in SiC Epi-Films. Materials Science Forum, 1998, 264-268, 653-656.	0.3	6
63	Aluminum Doping of Epitaxial Silicon Carbide Grown by Hot-Wall CVD; Effect of Process Parameters. Materials Science Forum, 2002, 389-393, 203-206.	0.3	6
64	Growth of High Quality p-Type 4H-SiC Substrates by HTCVD. Materials Science Forum, 2003, 433-436, 21-24.	0.3	6
65	Stacking Fault Formation in Highly Doped 4H-SiC Epilayers during Annealing. Materials Science Forum, 2003, 433-436, 253-256.	0.3	6
66	Very High Growth Rate of 4H-SiC Using MTS as Chloride-Based Precursor. Materials Science Forum, 0, 600-603, 115-118.	0.3	6
67	Single Crystal and Polycrystalline 3C-SiC for MEMS Applications. Materials Science Forum, 0, 615-617, 625-628.	0.3	6
68	Defects in 4H-SiC Layers Grown by Chloride-Based Epitaxy. Materials Science Forum, 0, 615-617, 373-376.	0.3	6
69	High Growth Rate with Reduced Surface Roughness during On-Axis Homoepitaxial Growth of 4H-SiC. Materials Science Forum, 2011, 679-680, 115-118.	0.3	6
70	Chloride Based CVD of 3C-SiC on (0001) \pm -SiC Substrates. Materials Science Forum, 2011, 679-680, 75-78.	0.3	6
71	Mercury-related luminescent center in silicon. Physical Review B, 1993, 47, 13309-13313.	1.1	5
72	Changes in the Exciton-Related Photoluminescence of 4H- and 6H-SiC Induced by Uniaxial Stress. Materials Science Forum, 1998, 264-268, 489-492.	0.3	5

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73	Photoluminescence Study of CVD Layers Highly Doped with Nitrogen. Materials Science Forum, 2000, 338-342, 619-622.	0.3	5
74	Pseudo-Donors in SiC. Materials Science Forum, 2000, 338-342, 647-650.	0.3	5
75	The Effect of Hydrogen Diffusion in p- and n-Type SiC Schottky Diodes at High Temperatures. Materials Science Forum, 2002, 389-393, 1419-1422.	0.3	5
76	Electron Paramagnetic Resonance of Shallow Phosphorous Centers in 4H- and 6H-SiC. Materials Science Forum, 2005, 483-485, 515-518.	0.3	5
77	6H-Type Zigzag Faults in Low-Doped 4H-SiC Epitaxial Layers. Materials Science Forum, 0, 645-648, 347-350.	0.3	5
78	Annealing Effects on Electrical and Optical Properties of N-ZnO/P-Si Heterojunction Diodes. Advanced Materials Research, 2011, 324, 233-236.	0.3	5
79	Comparison of Bottom-Up and Top-Down 3C-SiC NWFETs. Materials Science Forum, 0, 858, 1001-1005.	0.3	5
80	Power Schottky and p-n Diodes on SiC Epi-Wafers with Reduced Micropipe Density. Materials Science Forum, 2002, 389-393, 1173-1176.	0.3	4
81	Nitrogen Delta Doping in 4H-SiC Epilayers. Materials Science Forum, 2003, 433-436, 153-156.	0.3	4
82	Intrinsic Defects in HPSI 6H-SiC: an EPR Study. Materials Science Forum, 2008, 600-603, 381-384.	0.3	4
83	Large area mapping of the alloy composition of Al _x Ga _{1-x} N using infrared reflectivity. Physica Status Solidi - Rapid Research Letters, 2009, 3, 145-147.	1.2	4
84	Some Aspects of the Photoluminescence and Raman Spectroscopy of (10-10)- and (11-20)-Oriented 4H and 6H Silicon Carbide. Materials Science Forum, 1998, 264-268, 469-472.	0.3	3
85	Enlarging the Usable Growth Area in a Hot-Wall Silicon Carbide CVD Reactor by Using Simulation. Materials Science Forum, 2001, 353-356, 99-102.	0.3	3
86	Growth Characteristics of SiC in a Hot-Wall CVD Reactor with Rotation. Materials Science Forum, 2002, 389-393, 191-194.	0.3	3
87	Predicting Growth Rates of SiC Epitaxial Layers Grown by Hot-Wall Chemical Vapor Deposition. Materials Science Forum, 2002, 389-393, 219-222.	0.3	3
88	A Comparison of MESFETs on Different 4H-Silicon Carbide Semi-Insulating Substrates. Materials Science Forum, 2003, 433-436, 737-740.	0.3	3
89	Growth and Photoluminescence Study of Aluminium Doped SiC Epitaxial Layers. Materials Science Forum, 2007, 556-557, 97-100.	0.3	3
90	Contact-Less Electrical Defect Characterization of Semi-Insulating 6H-SiC Bulk Material. Materials Science Forum, 2008, 600-603, 405-408.	0.3	3

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91	On-Axis Homoepitaxy on Full 4H-SiC Wafer for High Power Applications. Materials Science Forum, 0, 615-617, 133-136.	0.3	3
92	Concentrated Chloride-Based Epitaxial Growth of 4H-SiC. Materials Science Forum, 0, 645-648, 95-98.	0.3	3
93	Observation of Bistable Defects in Electron Irradiated N-Type 4H-SiC. Materials Science Forum, 0, 679-680, 249-252.	0.3	3
94	600 V PIN Diodes Fabricated Using On-Axis 4H Silicon Carbide. Materials Science Forum, 2012, 717-720, 969-972.	0.3	3
95	Applications of Vapor-Liquid-Solid Selective Epitaxy of Highly p-Type Doped 4H-SiC: PiN Diodes with Peripheral Protection and Improvement of Specific Contact Resistance of Ohmic Contacts. Materials Science Forum, 0, 778-780, 639-644.	0.3	3
96	Important Nonradiative Grown-In Defects in MBE-Grown Si and SiGe/Si Heterostructures. Materials Science Forum, 1995, 196-201, 473-478.	0.3	2
97	Near Band-Gap Emission in V-Implanted and Annealed 4H-SiC. Materials Science Forum, 1998, 264-268, 497-500.	0.3	2
98	Bound Exciton Recombination in Electron Irradiated 4H-SiC. Materials Science Forum, 1998, 264-268, 477-480.	0.3	2
99	Epitaxial Growth of 4H-SiC in a Vertical Hot-Wall CVD Reactor: Comparison between Up- and Down-Flow Orientations. Materials Science Forum, 2001, 353-356, 91-94.	0.3	2
100	Influence of Epitaxial Layer on SiC Schottky Diode Gas Sensors Operated under High-Temperature Conditions. Materials Science Forum, 2002, 389-393, 1423-1426.	0.3	2
101	Electrical Characterization of High-Voltage 4H-SiC Diodes on High-Temperature CVD-Grown Epitaxial Layers. Materials Science Forum, 2002, 389-393, 1285-1288.	0.3	2
102	Correlation between Electrical and Optical Mapping of Boron Related Complexes in 4H-SiC. Materials Science Forum, 2003, 433-436, 423-426.	0.3	2
103	Doping-Related Strain in n-Doped 4H-SiC Crystals. Materials Science Forum, 2003, 433-436, 269-272.	0.3	2
104	Properties of the Bound Excitons Associated to the 3838Å... Line in 4H-SiC and the 4182Å... Line in 6H-SiC. Materials Science Forum, 2004, 457-460, 549-554.	0.3	2
105	Growth of Homoepitaxial Films on 4H-SiC(11-20) and 8° Off-Axis 4H-SiC(0001) Substrates and their Characterization. Materials Science Forum, 2004, 457-460, 221-224.	0.3	2
106	Shallow P Donors in 3C-, 4H- and 6H-SiC. Materials Science Forum, 2006, 527-529, 593-596.	0.3	2
107	Photoluminescence of Phosphorous Doped SiC. Materials Science Forum, 2006, 527-529, 589-592.	0.3	2
108	Influence of Cooling Rate after High Temperature Annealing on Deep Levels in High-Purity Semi-Insulating 4H-SiC. Materials Science Forum, 2007, 556-557, 371-374.	0.3	2

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109	Thick Epilayer for Power Devices. Materials Science Forum, 2007, 556-557, 47-52.	0.3	2
110	Chloride-Based SiC Epitaxial Growth. Materials Science Forum, 2009, 615-617, 89-92.	0.3	2
111	Metastable Defects in Low-Energy Electron Irradiated <i>n</i> -Type 4H-SiC. Materials Science Forum, 2010, 645-648, 435-438.	0.3	2
112	Chloride-based CVD of 3C-SiC Epitaxial Layers on On-axis 6H (0001) SiC Substrates. , 2010, , .		2
113	Chloride-Based CVD of 4H-SiC at High Growth Rates on Substrates with Different Off-Angles. Materials Science Forum, 2012, 717-720, 113-116.	0.3	2
114	CVD Heteroepitaxial Growth of 3C-SiC on 4H-SiC (0001) Substrates. Materials Science Forum, 0, 717-720, 189-192.	0.3	2
115	CVD Growth of 3C-SiC on 4H-SiC Substrate. Materials Science Forum, 2012, 711, 16-21.	0.3	2
116	Infrared Optical Properties of 3C, 4H and 6H Silicon Carbide. Materials Science Forum, 2003, 433-436, 329-332.	0.3	1
117	Investigation of the Electronic Structure of the UD-4 Defect in 4H-SiC by Optical Techniques. Materials Science Forum, 2006, 527-529, 461-464.	0.3	1
118	Titanium Related Luminescence in SiC. Materials Science Forum, 0, 600-603, 461-464.	0.3	1
119	The Electronic Structure of the UD-4 Defect in 4H, 6H and 15R SiC. Materials Science Forum, 0, 600-603, 397-400.	0.3	1
120	Improved SiC Epitaxial Material for Bipolar Applications. Materials Research Society Symposia Proceedings, 2008, 1069, 1.	0.1	1
121	Wave-Function Symmetry and the Properties of Shallow P Donors in 4H SiC. Materials Science Forum, 0, 600-603, 445-448.	0.3	1
122	AlGa _N Multiple Quantum Wells and AlN Grown in a Hot-wall MOCVD for Deep UV Applications. ECS Transactions, 2009, 25, 837-844.	0.3	1
123	Optical and Structural Properties of In-Grown Stacking Faults in 4H-SiC Epilayers. Materials Science Forum, 0, 645-648, 307-310.	0.3	1
124	Effect of Inter-Well Coupling between 3C and 6H in-Grown Stacking Faults in 4H-SiC Epitaxial Layers. Materials Science Forum, 0, 679-680, 314-317.	0.3	1
125	Electrical and Optical Properties of High-Purity Epilayers Grown by the Low-Temperature Chloro-Carbon Growth Method. Materials Science Forum, 2012, 717-720, 129-132.	0.3	1
126	Low Temperature Photoluminescence Investigation of 3-Inch SiC Wafers for Power Device Applications. Materials Science Forum, 0, 711, 164-168.	0.3	1

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127	Structural Investigation of Heteroepitaxial 3C-SiC Grown on 4H-SiC Substrates. Materials Science Forum, 0, 740-742, 319-322.	0.3	1
128	Optical Properties of the Niobium Centre in 4H, 6H, and 15R SiC. Materials Science Forum, 0, 740-742, 405-408.	0.3	1
129	Photoluminescence of 8H-SiC. Materials Science Forum, 0, 740-742, 347-350.	0.3	1
130	Ga Bound Excitons in 6H-SiC. Materials Science Forum, 1995, 196-201, 91-96.	0.3	0
131	Defect Formation and Recombination Processes in p-Type Modulation-Doped Si Epilayers. Materials Science Forum, 1995, 196-201, 479-484.	0.3	0
132	Optical Properties of Aluminium and Nitrogen in Compensated 4H-SiC Epitaxial Layers. Materials Research Society Symposia Proceedings, 2000, 640, 1.	0.1	0
133	Donor-Acceptor Pair Luminescence of Phosphorus-Aluminum and Nitrogen-Aluminum Pairs in 4H SiC. Materials Science Forum, 2006, 527-529, 601-604.	0.3	0
134	CVD of 6H-SiC on Non-Basal Quasi Polar Faces. Materials Science Forum, 2007, 556-557, 73-76.	0.3	0
135	Growth of 4H-SiC Epitaxial Layers on 4° Off-Axis Si-Face Substrates. Materials Science Forum, 0, 615-617, 81-84.	0.3	0
136	Temperature Dependence and Selective Excitation of the Phosphorus Related Photoluminescence in 4H-SiC. Materials Science Forum, 2009, 615-617, 263-266.	0.3	0
137	Donor-Acceptor Pair Luminescence of P-Al and N-Al Pairs in 3C-SiC and the Ionization Energy of the P Donor. Materials Science Forum, 0, 679-680, 245-248.	0.3	0
138	Electronic Configuration of Tungsten in 4H-, 6H-, and 15R-SiC. Materials Science Forum, 2012, 717-720, 211-216.	0.3	0
139	Comparative Study on Dry Etching of 1±- and 1²-SiC Nano-Pillars. Materials Science Forum, 2013, 740-742, 817-820.	0.3	0
140	Chemical Vapor Deposition of Boron Nitride Thin Films on SiC. Materials Science Forum, 2015, 821-823, 990-994.	0.3	0
141	Photoluminescence of 10H-SiC. Materials Science Forum, 2016, 858, 269-273.	0.3	0
142	Characteristics of Low-Temperature Solution-Processed Boron Nitride Thin Films for Flexible Nanoelectronics. Journal of Nanoscience and Nanotechnology, 2017, 17, 8567-8570.	0.9	0